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PATENT AP20 new Docket No. MIT-166 JAN 2006

Particulars of prior application:

International Serial No.: PCT/US2004/024747 International Filing Date: July 29, 2004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT(S):

Liu et al.

SERIAL NO.:

Not yet assigned

GROUP NO.:

Not yet assigned

FILING DATE:

Herewith

EXAMINER:

Not yet assigned

TITLE:

METHOD AND STRUCTURE OF STRAIN CONTROL OF SIGE

BASED PHOTODETECTORS AND MODULATORS

Mail Stop PCT Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. In accordance with the U.S. Patent Office's partial waiver of the requirement under 37 C.F.R. 1.98(a)(2)(i), only copies of the foreign patents and non-patent publications are enclosed.

REMARKS

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

	(1)	within three (3) months of the filing date of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the date of entry of the national stage as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the first Office action on the merits, or before the mailing of a first Office action after the				
	(2)	filing of a request for continued examination under 37 C.F.R. 1.114; or after the period defined in (1) but before the mailing date of a final action or a notice of allowance under 37 C.F.R. 1.311, and				
		the requisite Statement is below, OR				

Information Disclosure Statement Attorney Docket No. MIT-166 Page 2 of 2

1420 Res d PETATO 31 JAN 2006

		the requisite fee under 37 C.F.I	R. 1.17(p), namely \$180.00 , is included herein, or					
	(3)	after the mailing date of a fina payment of the issue fee, AND	inal action or notice of allowance but before the ND					
		the requisite Statement is below	v, AND					
		the requisite petition fee under herein.	37 C.F.R. 1.17(p), namely \$180.00 is included					
	•	• •	atents and publications listed on the attached herein, be made of record in this application.					
		STATE	MENT					
As either tha	-	d under 37 C.F.R. 1.97(e), Applica	ant(s), through the undersigned, hereby state					
[Statement was first cited office in a counterpart for	contained in the Information Disclosure in any communication from a foreign patent reign application not more than three months information Disclosure Statement; or					
]		was cited in a communication, and, to statement after making recontained in the Informational designated in the statement and the statemen	ontained in the Information Disclosure Statement ation from a foreign patent office in a counterpart to the knowledge of the person signing this asonable inquiry, no item of information ion Disclosure Statement was known to any 37 C.F.R. 1.56(c) more than three months prior ation Disclosure Statement.					
Date: Reg. No.	<u>Jan.</u> 44,381	31, 2004 N	Jatasha C. Us Attorney for Applicant(s) Goodwin Procter LLP					
Tel. No.: Fax No.: VER 12/	(617)5	523-1231 B	Exchange Place Boston, Massachusetts 02109 Customer No. 051414					

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IAP20 Rec'd FCT/770 31 JAN 2006 SHEET 1 OF 1

FORM PTO - 1449					ATTORNEY DOCKET NO.: MIT-166							
INFORMATION DISCLOSURE STATEMENT					NT	APPLICA	NT(S):	Liu et al.				
						SERIAL N	10.:	Not Yet Assigned				
						FILING D	ATE:	Herewith				
						GROUP:		Not Yet Assigned				
U.S. PATENT DOCUMENTS												
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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY		CLASS	SUB CLASS	FILING DATE		ABSTRACT ENGINEERS (Y/N)		
	B1	WO 03/105189	12/18/2003	W	0							
	B2	WO 04/001857	12/31/2003	W	0							
	ОТ	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)										
	C1		Boyanov, et al., "Growth of epitaxial CoSi2 on SiGe (001)", <u>Journal of Applied Physics</u> , American Institute of Physics. New York, US. 86(3):1355-1362 (1999).									
	C2		Buchal et al., "Ultrafast Si-based MSM mesa photodetectors with optical waveguide connection," Materials Science in Semiconductor Processing, 3:399-403 (2000). XP001205581									
	C3		Steegen et al., "Silicide-induced stress in Si: origin and consequences for MOS technologies," <u>Materials Science and Engineering R: Reports</u> , Elsevier Sequoia S.A., Lausanne, CH. 38(1):1-53 (2002).									
	C4	and Ge hetero	Yodo et al., "Influences of off-angle and off-direction of substrate on cyrstlline quality of GaAs and Ge heteroepitaxial films grown on vicinal Si (110) substrates by molecular-beam epitaxy", <u>lournal of Crystal Growth</u> . North-Holland Publishing Co., Amsterdam, NL. 209(4):724-733 (2000). XP004198396									
	C5	C5 International Search Report for PCT/US2004/024747 dated March 22, 2005.										
EXAMINER					DATE CONSIDERED							